

MIG10120H

1200V Silicon Carbide Schottky Diode

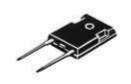
DESCRIPTION :

- Negligible reverse recovery
- High Speed Switching
- Positive temperature Coefficient
- Temperature Independent Switching
- RoHS Compliant

TYPICAL APPLICATIONS :

- Switch mode power supplies
- Solar inverters
- Data Center
- Uninterruptible power supplies (UPS)

VRRM	1200V	
I _F	10A (TC=158°C)	
Q _C	52nC	



TO-247AC

MAXIMUM RATINGS (at T_C = 25 °C, unless otherwise specified)

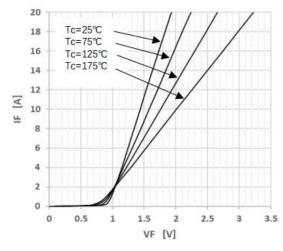
Characteristic	Condition	Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V _{RRM}	1200	V
Continuous Forward Current	Tc=25℃ Tc=135℃ Tc=158℃	I _F	35 17 10	A
Non-Repetitive Forward Surge Current	Tc=25°C , t_P=10ms, Half sine pulse Tc=110°C , t_P=10ms, Half sine pulse	I _{FSM}	59 45	А
Repetitive Peak Forward Surge Current	Tc=25 $^\circ\!\!\mathbb{C}$, tp=10ms, Half sine pulse	I _{FRM}	50	А
i ² t value	Tc=25℃ , tբ=10ms Tc=110℃ , tբ=10ms	∫ i²dt	17 10	A ² S
Power dissipation	Tc=25℃ Tc=110℃ Tc=150℃	P _{tot}	191 83 32	w
Operation Junction temperature		Tj	-55~+175	°C
Storage temperature		T _{STG}	-55~+175	°C

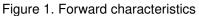
THERMAL CHARACTERISTICSCharacteristicConditionSymbolTypicalUnitThermal resistance,
junction - caseRth(j-C)0.787°C /W

ELECTRICAL CHARATERISTICS (at $T_c = 25$ °C, unless otherwise specified)

Characteristic	Symbol	Min.	Тур.	Max.	Unit
DC Blocking Voltage	V _{DC}	1200			V
Forward Voltage IF = 5A IF = 10A, Tc =25°C IF = 10A, Tc =175°C	V _F		1.20 1.43 2.0	1.7	V
Reverse Current VR = 1200V, Tc =25℃ VR = 1200V, Tc =175℃	I _R		2 4	60	uA
Total Capacitive Charge VR = 800V	Q _c		52		nC
Total capacitance VR = 1V, f =1MHz VR = 400V, f =1MHz VR = 800V, f =1MHz	С		546 47 41		pF
Capacitance Stored Energy VR = 800 V	Ec		15.86		uJ

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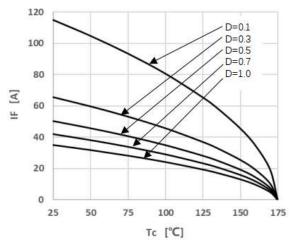


Figure 3. Peak Forward Current Derating

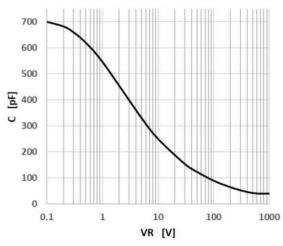


Figure 5. Capacitance vs. Reverse Voltage

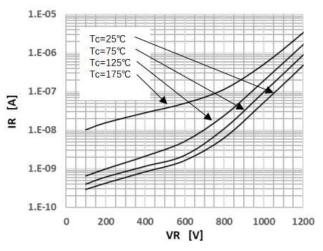


Figure 2. Reverse characteristics

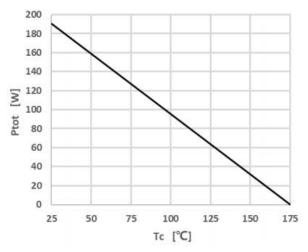


Figure 4. Power Dissipation

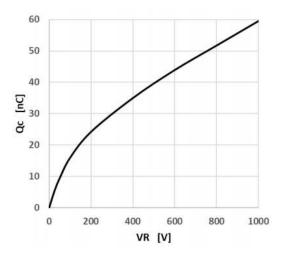


Figure 6. Capacitance Charge vs. Reverse Voltage

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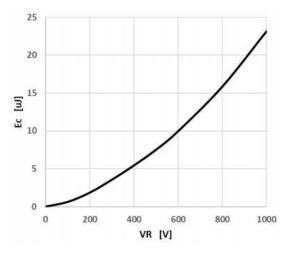


Figure 7. Capacitance Stored Energy

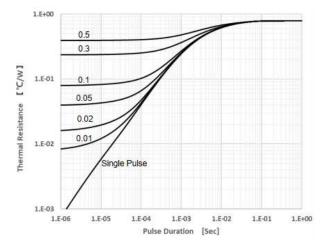
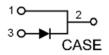
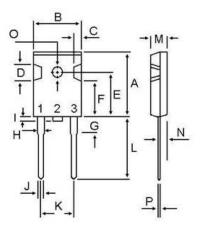


Figure 8. Transient Thermal Impedance

Circuit diagram



TO-247AC Package outlines : Dimensions in (mm)



DIM	MILLIMETERS		
DIM	MIN	MAX	
Α	20.63	22.38	
В	15.38	16.20	
С	1.90	2.70	
D	5.10	6.10	
E	14.81	15.22	
F	11.72	12.84	
G	3.75	4.35	
Н	1.82	2.46	
I		1.25	
J	0.89	1.53	
K	10.52	11.32	
L	18.50	21.50	
М	4.68	5.36	
Ν	2.40	2.80	
0	3.25	3.65	
Р	0.55	0.70	



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